

SEMICONDUCTOR LASER ELEMENT AND ITS MANUFACTURE

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Abstract of JP11312840

PROBLEM TO BE SOLVED: To provide a technology for extending the element life of a semiconductor laser element of gallium nitride compound semiconductor and for reducing series resistance of the semiconductor element.

SOLUTION: This is a gallium nitride compound semiconductor laser element in which a conductive selective growth mask 104 is formed on a gallium nitride compound semiconductor, on which at least a pair of clad layer 106 and an active layer 107 are formed. Here, with an element structure for which the conductive selective growth mask 104 functions as a current path, a reliable current preventing gallium nitride compound semiconductor laser element with reduced threshold current is realized.

